

P-Channel 150-V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | | |
|---------------------|----------------------------------|--------------------|-----------------------|--|--|--|
| V _{DS} (V) | $R_{DS(on)}(\Omega)$ | I _D (A) | Q _g (Typ.) | | | |
| - 150 | 1.2 at V _{GS} = - 10 V | - 0.69 | 7.7 | | | |
| | 1.3 at V _{GS} = - 6.0 V | - 0.66 | 7.7 | | | |

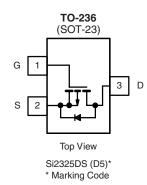
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- Ultra Low On-Resistance
- Small Size



APPLICATIONS

• Active Clamp Circuits in DC/DC Power Supplies



Ordering Information: Si2325DS -T1-E3 (Lead (Pb)-free)

Si2325DS -T1-GE3 (Lead (Pb)-free and Halogen-free)

| ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted | | | | | | |
|---|-----------------------------------|------------------|--------------|--------|----|--|
| Parameter | Symbol | 5 s | Steady State | Unit | | |
| Drain-Source Voltage | | V _{DS} | - 150 | | V | |
| Gate-Source Voltage | | V _{GS} | ± 20 | | | |
| Continuous Brain Comment /T 450 9008 b | T _A = 25 °C | I _D | - 0.69 | - 0.53 | | |
| Continuous Drain Current (T _J = 150 °C) ^{a, b} | T _A = 70 °C | | - 0.55 | - 0.43 | | |
| Pulsed Drain Current | | I _{DM} | - 1.6 | | Α | |
| Continuous Source Current (Diode Conduction) ^{a, b} | | I _S | - 1.0 | - 0.6 | | |
| Single Pulse Avalanche Current | L = 1.0 mH | I _{AS} | 4 | .5 | | |
| Single Pulse Avalanche Energy | L = 1.0 MH | E _{AS} | 1.01 | | mJ | |
| Mariana Barra Biratani a h | T _A = 25 °C | P _D | 1.25 | 0.75 | W | |
| Maximum Power Dissipation ^{a, b} | T _A = 70 °C | ' ⁻ D | 0.8 | 0.48 | " | |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | - 55 · | to 150 | °C | | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|--|--------------|-------------------|---------|------|------|--|
| Parameter | Symbol | Typical | Maximum | Unit | | |
| Maniana Institut to Analisma | t ≤ 5 s | D | 75 | 100 | | |
| Maximum Junction-to-Ambient ^a | Steady State | R_{thJA} | 120 | 166 | °C/W | |
| Maximum Junction-to-Foot (Drain) | Steady State | R _{thJF} | 40 | 50 | | |

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.

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| SPECIFICATIONS T _J = 25 °C, unless otherwise noted | | | | | | | |
|--|----------------------|---|--------|------|-------|------|--|
| | | | Limits | | | | |
| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V _{(BR)DSS} | $V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$ | - 150 | | | V | |
| Gate-Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}$, $I_D = -250 \mu A$ | - 2.5 | | - 4.5 | v | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 V, V_{GS} = \pm 20 V$ | | | ± 100 | nA | |
| Zero Gate Voltage Drain Current | laco | $V_{DS} = -150 \text{ V}, V_{GS} = 0 \text{ V}$ | | | - 1 | ^ | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = - 150 V, V _{GS} = 0 V, T _J = 55 °C | | | - 10 | μΑ | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \le$ - 15 V, $V_{GS} = 10 \text{ V}$ | - 1.6 | | | Α | |
| Durin Course On Beninters of | B | V _{GS} = - 10 V, I _D = - 0.5 A | | 1.0 | 1.2 | | |
| Drain-Source On-Resistance ^a | R _{DS(on)} | $V_{GS} = -6.0 \text{ V}, I_D = -0.5 \text{ A}$ | | 1.05 | 1.3 | Ω | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = - 15 V, I _D = - 0.5 A | | 2.2 | | S | |
| Diode Forward Voltage | V_{SD} | I _S = - 1.0 A, V _{GS} = 0 V | | 0.7 | - 1.2 | V | |
| Dynamic ^b | | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = -75 \text{ V}, V_{GS} = 10 \text{ V},$ | | 7.7 | 12 | | |
| Gate-Source Charge | Q_{gs} | $V_{DS} = -75 \text{ V}, V_{GS} = 10 \text{ V},$ $I_{D} \cong -0.5 \text{ A}$ | | 1.5 | | nC | |
| Gate-Drain Charge | Q_{gd} | .D = 0.0 / t | | 2.5 | | | |
| Gate Resistance | R_{g} | f = 1.0 MHz | | 9 | | Ω | |
| Input Capacitance | C _{iss} | | | 340 | 510 | | |
| Output Capacitance | C _{oss} | $V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | | 30 | | pF | |
| Reverse Transfer Capacitance | C _{rss} | | | 16 | | | |
| Switching ^c | | | | | | | |
| Turn-On Time | t _{d(on)} | V 75 V D 75 O | | 7 | 11 | ns | |
| Turn-On Time | t _r | V_{DD} = - 75 V, R_L = 75 Ω $I_D \cong$ - 1.0 A, V_{GEN} = - 10 V | | 11 | 17 | | |
| Turn-Off Time | t _{d(off)} | $R_{g} = 6 \Omega$ | | 16 | 25 | | |
| Turr-Oil Tillie | t _f | y - | | 11 | 17 | | |
| Body Diode Reverse Recovery Charge | Q _{rr} | $I_F = 0.5 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}$ | | 90 | 135 | nC | |

Notes:

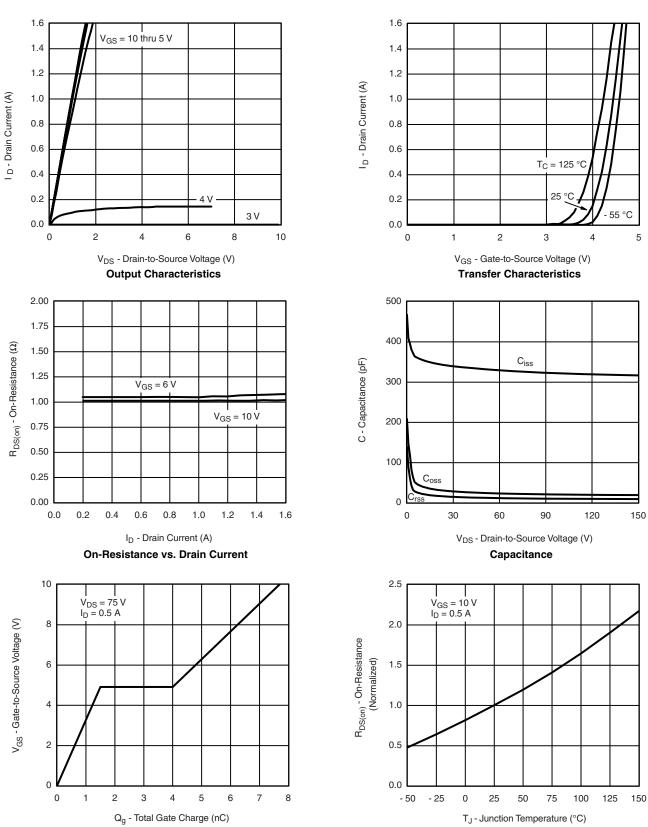
- a. Pulse test: PW \leq 300 μs duty cycle \leq 2 %.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



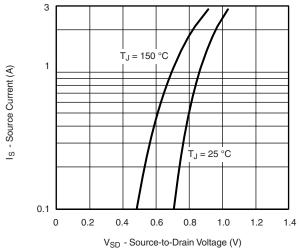
Gate Charge

On-Resistance vs. Junction Temperature

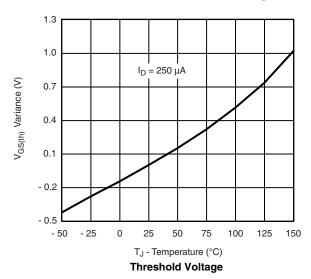
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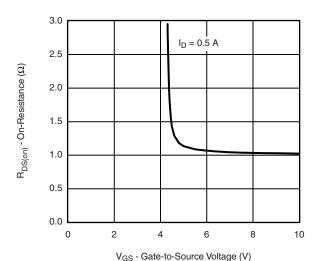
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

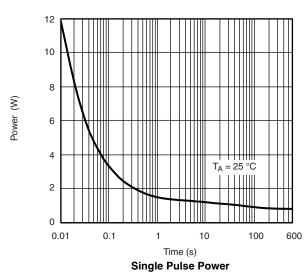


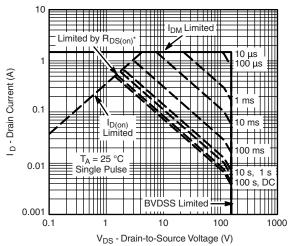
Source-Drain Diode Forward Voltage





On-Resistance vs. Gate-to-Source Voltage



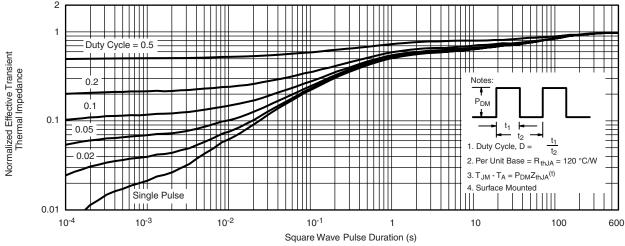


* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



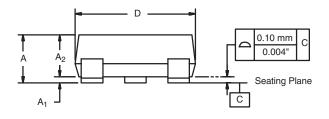
Normalized Thermal Transient Impedance, Junction-to-Ambient

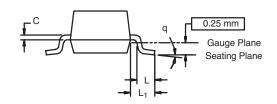
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SOT-23 (TO-236): 3-LEAD







| Dim - | MILLIN | IETERS | INCHES | | |
|--------------------------|----------|--------|------------|---------|--|
| | Min | Max | Min | Max | |
| Α | 0.89 | 1.12 | 0.035 | 0.044 | |
| A ₁ | 0.01 | 0.10 | 0.0004 | 0.004 | |
| A ₂ | 0.88 | 1.02 | 0.0346 | 0.040 | |
| b | 0.35 | 0.50 | 0.014 | 0.020 | |
| С | 0.085 | 0.18 | 0.003 | 0.007 | |
| D | 2.80 | 3.04 | 0.110 | 0.120 | |
| E | 2.10 | 2.64 | 0.083 | 0.104 | |
| E ₁ | 1.20 | 1.40 | 0.047 | 0.055 | |
| е | 0.95 BSC | | 0.0374 Ref | | |
| e ₁ | 1.90 BSC | | 0.0748 Ref | | |
| L | 0.40 | 0.60 | 0.016 | 0.024 | |
| L ₁ | 0.64 Ref | | 0.025 | 025 Ref | |
| S | 0.50 Ref | | 0.020 |) Ref | |
| q | 3° | 8° | 3° | 8° | |
| ECN: S-03946-Rev. K. 09- | Jul-01 | | | | |

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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE

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